

# RF Power MOSFET Transistor 60 W, 2 - 175 MHz, 28 V

Rev. V1

#### **Features**

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than bipolar devices
- RoHS Compliant

### **ABSOLUTE MAXIMUM RATINGS AT 25° C**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	65	V
Gate-Source Voltage	V <sub>GS</sub>	20	V
Drain-Source Current	I <sub>DS</sub>	12	Α
Power Dissipation	P <sub>D</sub>	159	W
Junction Temperature	TJ	200	°C
Storage Temperature	T <sub>STG</sub>	-65 to +150	°C
Thermal Resistance	$\theta_{\text{JC}}$	1.1	°C/W

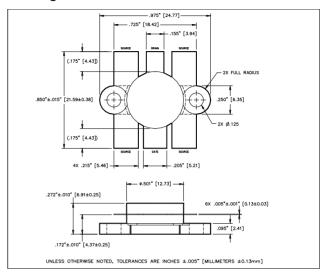
#### **TYPICAL DEVICE IMPEDANCE**

F (MHz)	Z <sub>IN</sub> (Ω)	Z <sub>LOAD</sub> (Ω)		
30	9.0 - j4.0 6.0 +j0.0			
50	10.0 - j6.5 5.0 + j2.0			
100	6.0 - j5.5	4.0 + j3.0		
200 1.1 - j3.0 2.0 + j1.9				
$V_{DD} = 28V$ , $I_{DQ} = 300$ mA, $P_{OUT} = 60$ W				

 $Z_{\text{IN}}$  is the series equivalent input impedance of the device from gate to source.

 $Z_{\text{LOAD}}$  is the optimum series equivalent load impedance as measured from drain to ground.

## **Package Outline**



LETTER	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
А	24.64	24.89	.970	.980
В	18.29	18.54	.720	.730
С	21.21	21.97	.835	.865
D	12.60	12.85	.496	.506
E	6.22	6.48	.245	.255
F	3.81	4.06	.150	.160
G	5.33	5.59	.210	.220
Н	5.08	5.33	.200	.210
J	3.05	3.30	.120	.130
K	2.29	2.54	.090	.100
L	4.06	4.57	.160	.180
М	6.68	7.49	.263	.295
N	.10	.15	.004	.006

#### **ELECTRICAL CHARACTERISTICS AT 25°C**

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	65	-	V	V <sub>GS</sub> = 0.0 V , I <sub>DS</sub> = 15.0 mA
Drain-Source Leakage Current	I <sub>DSS</sub>	-	3.0	mA	V <sub>GS</sub> = 28.0 V , V <sub>GS</sub> = 0.0 V
Gate-Source Leakage Current	I <sub>GSS</sub>	-	3.0	μA	V <sub>GS</sub> = 20.0 V , V <sub>DS</sub> = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	V <sub>DS</sub> = 10.0 V , I <sub>DS</sub> = 300.0 mA
Forward Transconductance	G <sub>M</sub>	1.5	-	S	$V_{DS}$ = 10.0 V , $I_{DS}$ = 3.0 A , $\Delta$ $V_{GS}$ = 1.0V, 80 $\mu$ s Pulse
Input Capacitance	C <sub>ISS</sub>	-	135	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	120	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C <sub>RSS</sub>	-	24	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Power Gain	G <sub>P</sub>	13	-	dB	$V_{DD}$ = 28.0 V, $I_{DQ}$ = 300 mA, $P_{OUT}$ = 60 W F =175 MHz
Drain Efficiency	ŋ <sub>D</sub>	60	-	%	$V_{DD}$ = 28.0 V, $I_{DQ}$ = 300 mA, $P_{OUT}$ = 60 W F =175 MHz
Load Mismatch Tolerance	VSWR-T	-	30:1	-	$V_{DD}$ = 28.0 V, $I_{DQ}$ = 300 mA, $P_{OUT}$ = 60 W F =175 MHz

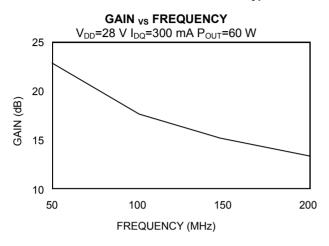
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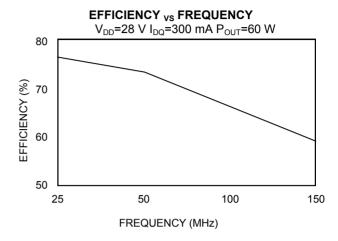


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# **Typical Broadband Performance Curves**





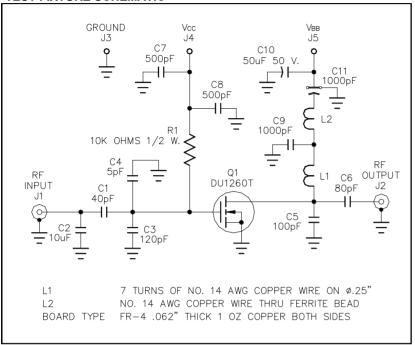
#### POWER OUTPUT vs POWER INPUT $V_{DD} = 28 \text{ V } I_{DQ} = 300 \text{ mA}$ 80 150MHz 100MHz POWER OUTPUT (W) 60 200MHz 40 20 0 0 0.5 1.5 2 2.5 2.75 3 POWER INPUT (W)



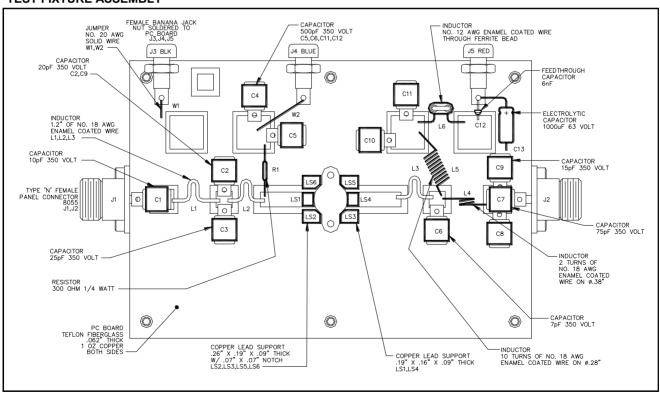
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#### **TEST FIXTURE SCHEMATIC**



### **TEST FIXTURE ASSEMBLY**



# **DU2860T**



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